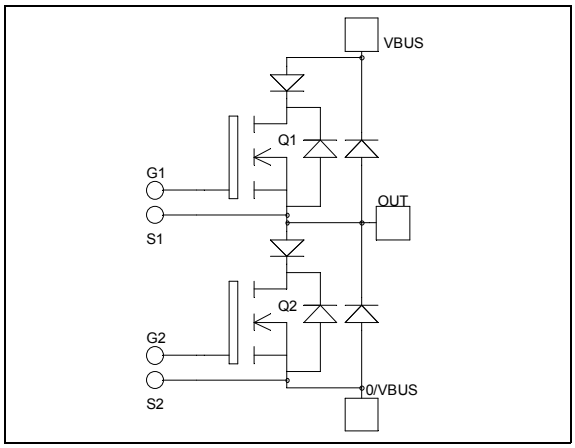
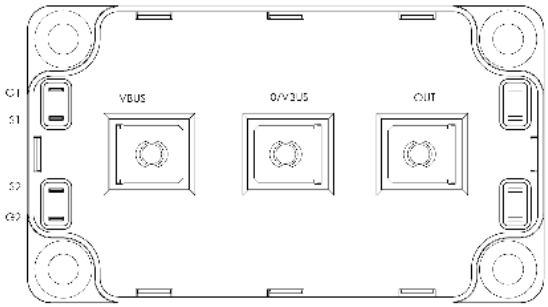
APTC80AM75SCG

Phase leg Series & SiC parallel diodes
Super Junction MOSFET Power Module

V_{DSS} = 800V
R_{DSon} = 75mΩ max @ Tj = 25°C
I_D = 56A @ Tc = 25°C





Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- ***CoolMOS™***
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
- ***Parallel SiC Schottky Diode***
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		800	V
I_D	Continuous Drain Current	T_c = 25°C	56	A
		T_c = 80°C	43	
I_{DM}	Pulsed Drain current		232	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		75	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	568	W
I_{AR}	Avalanche current (repetitive and non repetitive)		17	A
E_{AR}	Repetitive Avalanche Energy		0.5	mJ
E_{AS}	Single Pulse Avalanche Energy		670	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 800V	T_j = 25°C			100	µA
		V_{GS} = 0V, V_{DS} = 800V	T_j = 125°C			1000	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 28A				75	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 4mA		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				±200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		9015		pF
C_{oss}	Output Capacitance			4183		
C_{rss}	Reverse Transfer Capacitance			215		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 400V I_D = 56A		364		nC
Q_{gs}	Gate – Source Charge			48		
Q_{gd}	Gate – Drain Charge			184		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 533V I_D = 56A R_G = 1.2Ω		10		ns
T_r	Rise Time			13		
$T_{d(off)}$	Turn-off Delay Time			83		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 533V I_D = 56A, R_G = 1.2Ω		583		µJ
E_{off}	Turn-off Switching Energy			556		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 533V I_D = 56A, R_G = 1.2Ω		1020		µJ
E_{off}	Turn-off Switching Energy			684		
R_{thJC}	Junction to Case Thermal Resistance				0.22	°C/W

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1000			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1000V				300	µA
I_F	DC Forward Current		T_c = 80°C		120		A
V_F	Diode Forward Voltage	I_F = 120A			1.9	2.5	V
		I_F = 240A			2.2		
		I_F = 120A	T_j = 125°C		1.7		
t_{rr}	Reverse Recovery Time	I_F = 120A V_R = 667V di/dt = 400A/µs	T_j = 25°C		280		ns
			T_j = 125°C		350		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		1.52		µC
			T_j = 125°C		7.2		
R_{thJC}	Junction to Case Thermal Resistance					0.46	°C/W

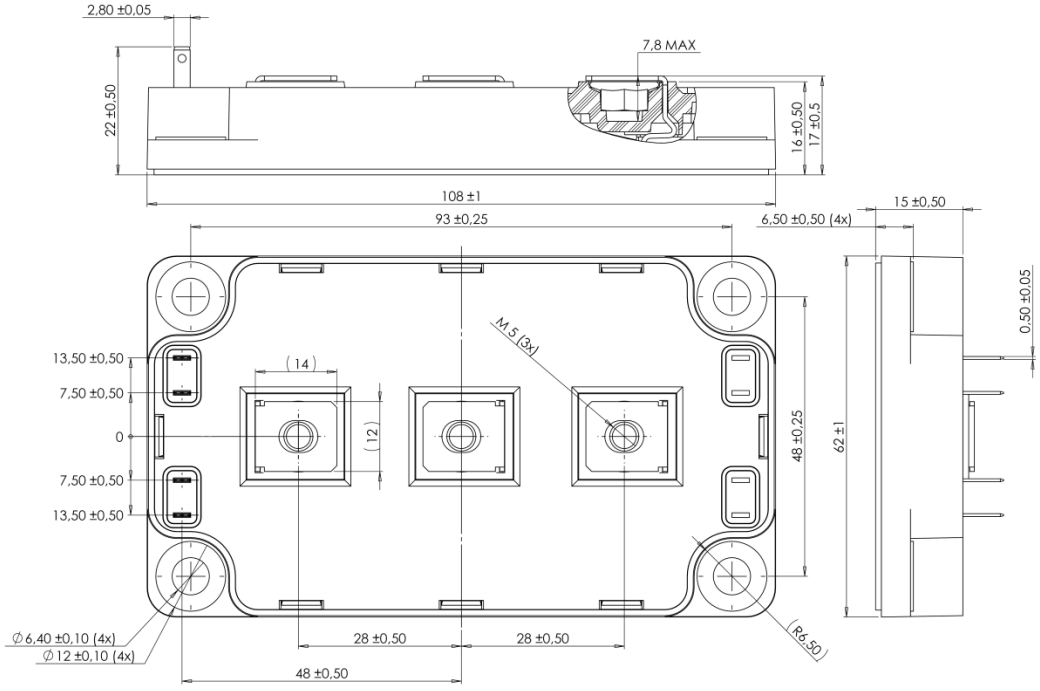
Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C		300	1200	µA
			T_j = 175°C		600	6000	
I_F	DC Forward Current		Tc = 100°C		30		A
V_F	Diode Forward Voltage	I_F = 30A	T_j = 25°C		1.6	1.8	V
			T_j = 175°C		2.6	3.0	
Q_C	Total Capacitive Charge	I_F = 30A, V_R = 1200V di/dt =1600A/µs			168		nC
Q	Total Capacitance	f = 1MHz, V_R = 200V			270		pF
		f = 1MHz, V_R = 400V			198		
R_{thJC}	Junction to Case Thermal Resistance					0.45	°C/W

Thermal and package characteristics

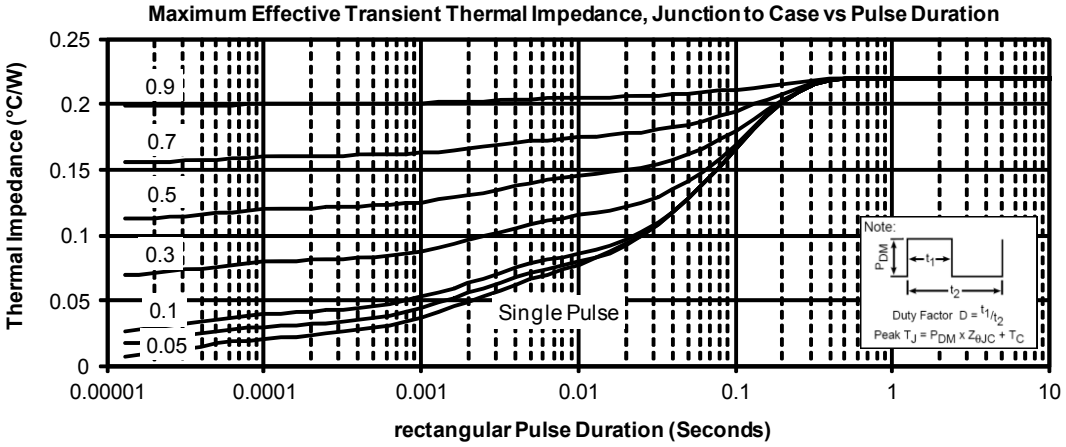
Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	150	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

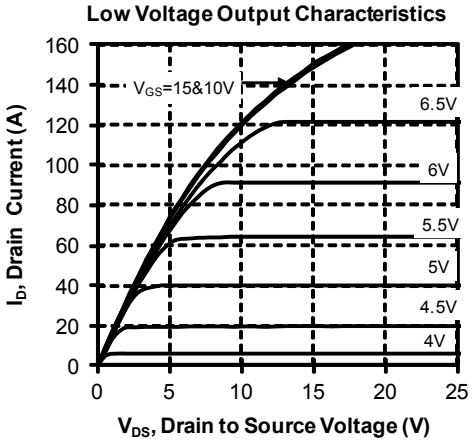
SP6 Package outline (dimensions in mm)

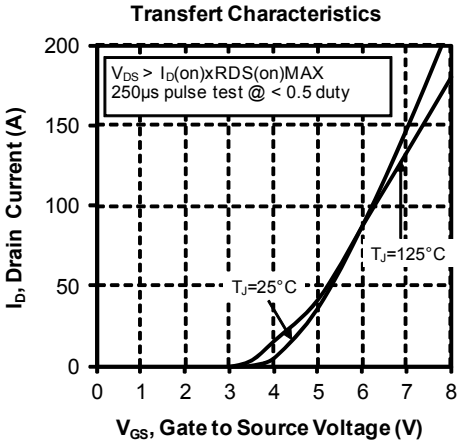


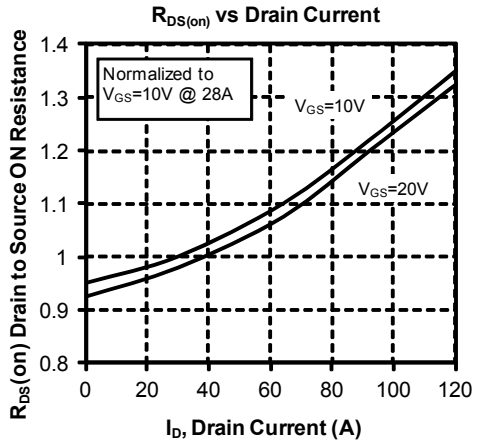
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

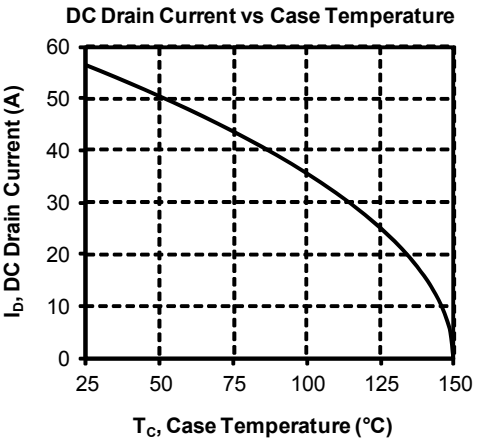
Typical CoolMOS Performance Curve



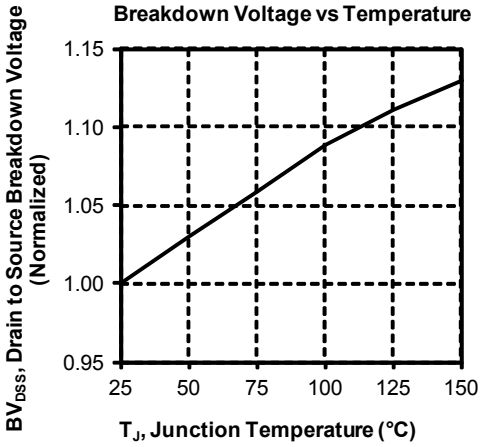




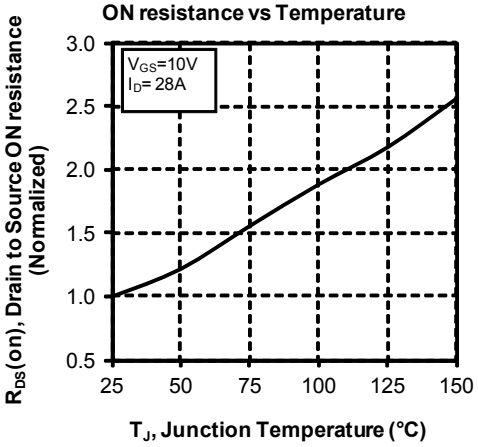




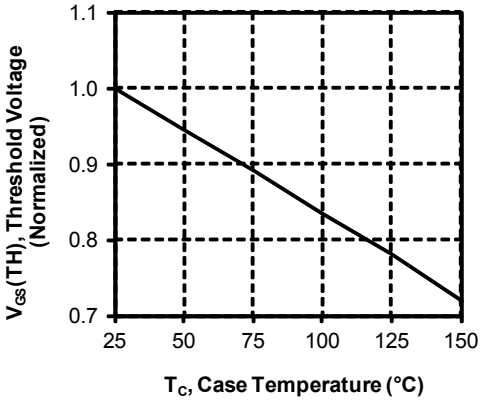
Breakdown Voltage vs Temperature



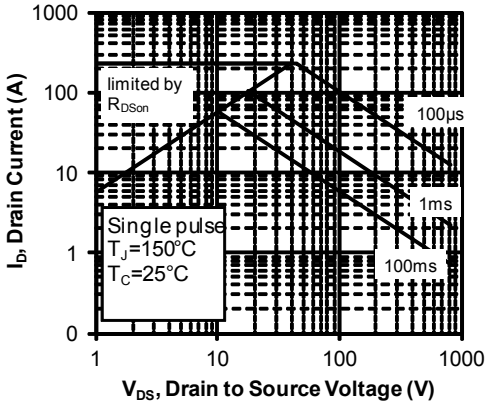
ON resistance vs Temperature



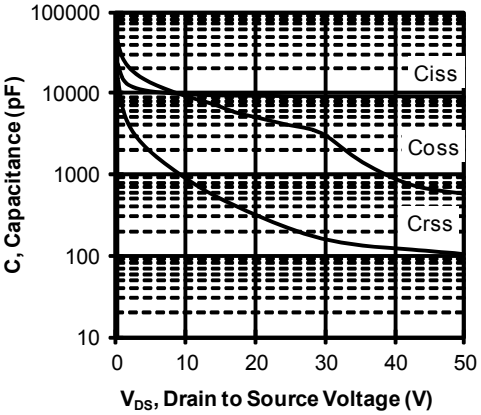
Threshold Voltage vs Temperature



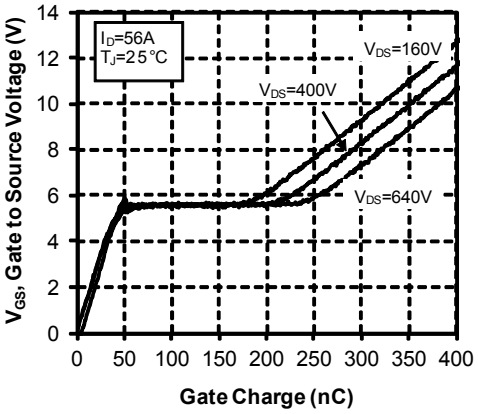
Maximum Safe Operating Area



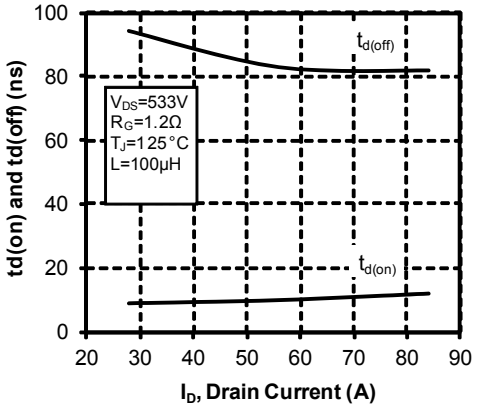
Capacitance vs Drain to Source Voltage



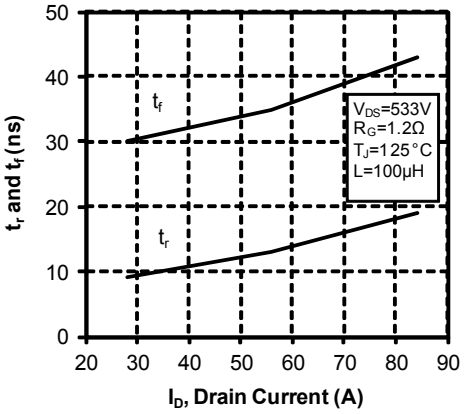
Gate Charge vs Gate to Source Voltage



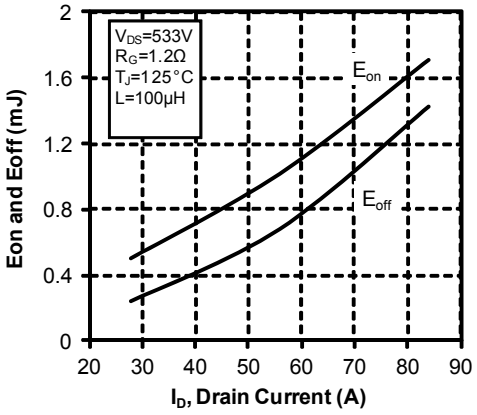
Delay Times vs Current



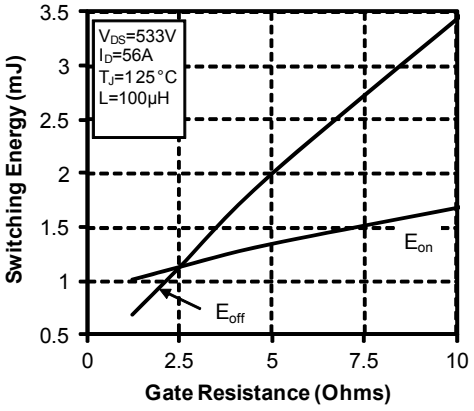
Rise and Fall times vs Current



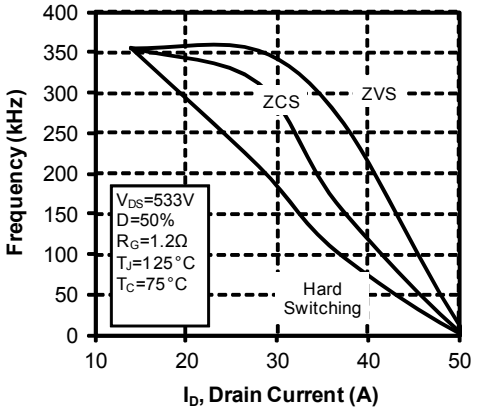
Switching Energy vs Current



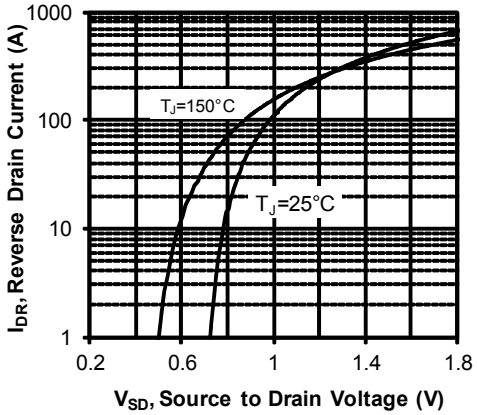
Switching Energy vs Gate Resistance



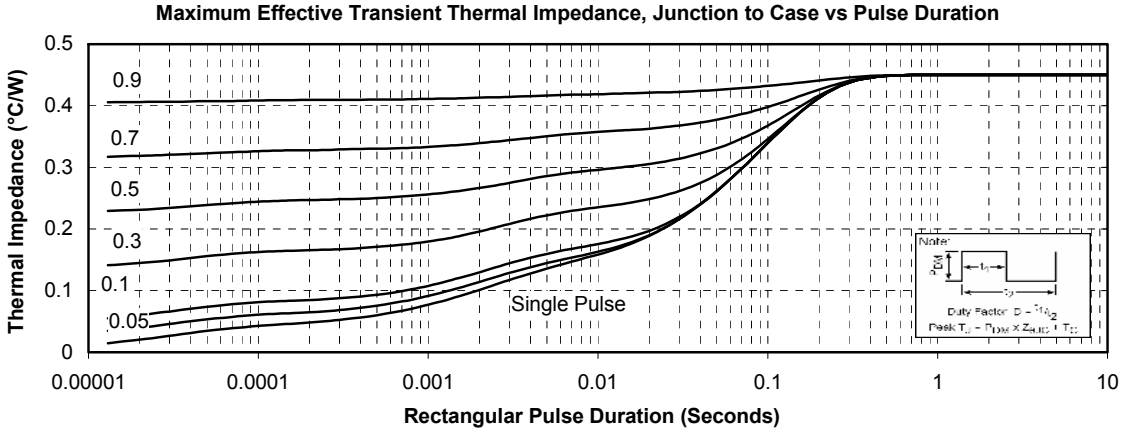
Operating Frequency vs Drain Current

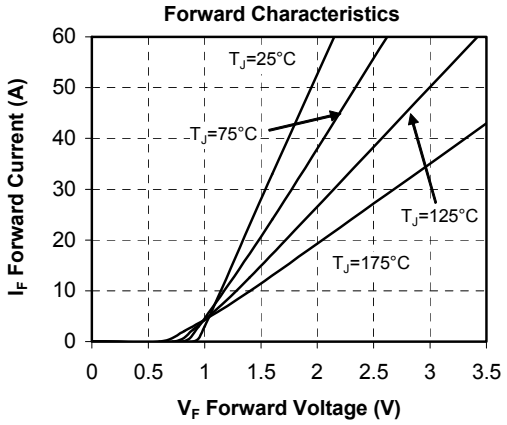


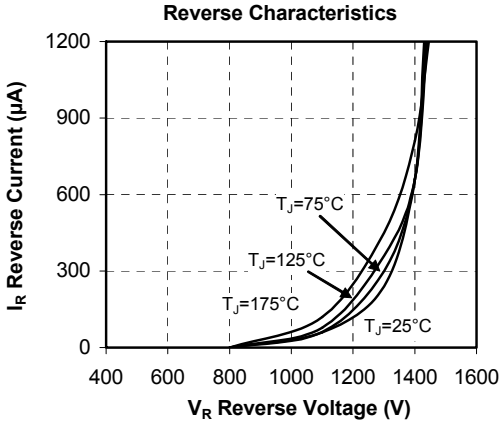
Source to Drain Diode Forward Voltage

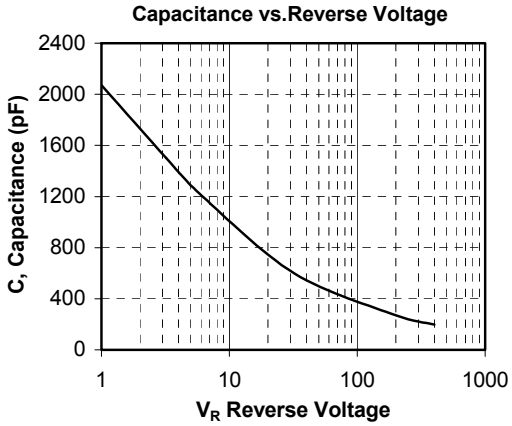


Typical SiC Diode Performance Curve









"COOLMOS™ comprise a new family of transistors developed by Infineon Technologies AG. "COOLMOS" is a trademark of Infineon Technologies AG".

DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.